

## FAST RECOVERY DIODES

- **Junction Size:** Rectangular 350 x 230 mils
- **Wafer Size:** 4"
- **V<sub>RRM</sub> Class:** 1000 to 1200 V
- **Passivation Process:** Glassivated MOAT
- **Reference IR Packaged Part:** 60EPF Series

### Major Ratings and Characteristics

Parameters	Units	Test Conditions
V <sub>FM</sub> Maximum Forward Voltage	1300 mV	T <sub>J</sub> = 25°C, I <sub>F</sub> = 60 A
V <sub>RRM</sub> Reverse Breakdown Voltage Range	1000 to 1200 V	T <sub>J</sub> = 25°C, I <sub>RRM</sub> = 100 μA (1)

(1) Nitrogen flow on die edge.

### Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	350 x 230 mils (8.89x5.84 mm) - see drawing
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	260 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

# IR340LM..CS05CB Series

Bulletin I0114J 05/00

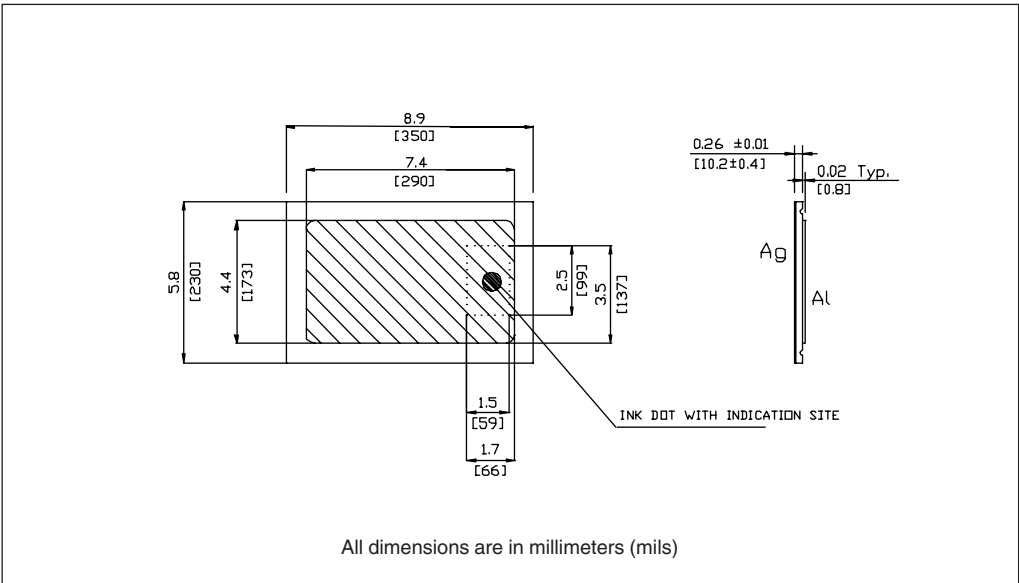
International  
**IR** Rectifier

## Ordering Information Table

Device Code							
IR	340	L	M	12	C	S05	CB
①	②	③	④	⑤	⑥	⑦	⑧
1	- International Rectifier Device						
2	- Chip Dimension in Mils						
3	- Type of Device: L = Wire Bondable Fast Recovery Diode						
4	- Passivation Process: M = Glassivated MOAT						
5	- Voltage code: Code x 100 = $V_{RRM}$						
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)						
7	- $T_{rr}$ code: S05 = 500 nsec						
8	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier						

**Available Class**  
10 = 1000 V  
12 = 1200 V

## Outline Table



## Wafer Layout

